

# **SMK1625F**

**Advanced N-Ch Power MOSFET** 

### SWITCHING REGULATOR APPLICATIONS

#### **Features**

• High Voltage :  $BV_{DSS}=250V(Min.)$ 

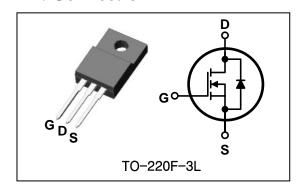
• Low C<sub>rss</sub> : C<sub>rss</sub>=49pF(Typ.)

• Low gate charge : Qg=22nC(Typ.) • Low  $R_{DS(on)}$  :  $R_{DS(on)}$ =0.27 $\Omega(Max.)$ 

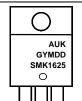
## **Ordering Information**

Type No.	Marking	Package Code
SMK1625F	SMK1625	TO-220F-3L

### **PIN Connection**



### **Marking Diagram**



Column 1: Manufacturer

Column 2: Production Information

e.g.) GYMDD

-. G : Factory management code

-. YMDD : Date Code (year, month, date)

Column 3: Device Code

## Absolute maximum ratings (T<sub>C</sub>=25°C unless otherwise noted)

Characteristic	Symbol		Rating	Unit
Drain-source voltage	$V_{DSS}$		250	V
Gate-source voltage		$V_{GSS}$	±30	V
Drain current (DC) *	т	T <sub>C</sub> =25℃	16	А
Diam current (DC)	$I_D$	T <sub>C</sub> =100 ℃	7.2	Α
Drain current (Pulsed) *		$I_{DM}$	64	А
Power dissipation		$P_D$	35	W
Avalanche current (Single) 2		$I_{AS}$	16	Α
Single pulsed avalanche energy ②		E <sub>AS</sub>	480	mJ
Avalanche current (Repetitive) ①		$I_{AR}$	16	Α
Repetitive avalanche energy ①	E <sub>AR</sub>		13.9	mJ
Junction temperature		$T_{\mathtt{J}}$	150	°C
Storage temperature range		$T_{stg}$	-55~150	C

<sup>\*</sup> Limited by maximum junction temperature

Characteristic		Symbol	Typ.	Max.	Unit
Thermal	Junction-case	$R_{th(J-C)}$	-	3.57	°C/W
resistance	Junction-ambient	$R_{th(J-A)}$	-	62.5	C/ VV

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# $\boldsymbol{Electrical\ Characteristics}\ (T_{\text{C}}\text{=}25^{\circ}\text{C}\ unless\ otherwise\ noted})$

Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Drain-source breakdown voltage	$BV_{DSS}$	I <sub>D</sub> =250uA, V <sub>GS</sub> =0V	250	-	-	V
Gate threshold voltage	$V_{GS(th)}$	I <sub>D</sub> =250uA, V <sub>DS</sub> =V <sub>GS</sub>	2.0	-	4.0	V
Drain-source cut-off current	$I_{DSS}$	V <sub>DS</sub> =250V, V <sub>GS</sub> =0V	-	-	1	uA
Gate leakage current	$I_{GSS}$	$V_{DS}$ =0V, $V_{GS}$ =±30V	-	-	±100	nA
Drain-source on-resistance ④	R <sub>DS(on)</sub>	$V_{GS} = 10V, I_D = 8.0A$	-	0.22	0.27	Ω
Forward transfer conductance ④	g <sub>fs</sub>	$V_{DS}$ =10V, $I_{D}$ =8.0A	-	10.5	-	S
Input capacitance	C <sub>iss</sub>		-	968	1275	
Output capacitance	C <sub>oss</sub>	$V_{GS}$ =0V, $V_{DS}$ =25V f=1 MHz	-	204	278	pF
Reverse transfer capacitance	C <sub>rss</sub>		-	49	64	
Turn-on delay time	t <sub>d(on)</sub>		-	15	-	
Rise time	t <sub>r</sub>	$R_{G}=125V$ , $I_{D}=16A$ $R_{G}=25\Omega$	-	130	-	no
Turn-off delay time	t <sub>d(off)</sub>		-	135	-	ns
Fall time	t <sub>f</sub>		-	105	-	
Total gate charge	$Q_g$	V <sub>DS</sub> =200V, V <sub>GS</sub> =10V	-	22	28	
Gate-source charge	$Q_{gs}$	I <sub>D</sub> =16A	-	7.1	-	nC
Gate-drain charge	$Q_{gd}$	34	-	5.9	-	

# Source-Drain Diode Ratings and Characteristics (T<sub>C</sub>=25°C unless otherwise noted)

		` ` `				
Characteristic	Symbol	<b>Test Condition</b>	Min.	Typ.	Max.	Unit
Source current (DC)	Is	Integral reverse diode	-	-	16	۸
Source current (Pulsed)	$I_{SM}$	in the MOSFET	-	-	64	Α
Forward voltage ④	$V_{SD}$	$V_{GS}$ =0V, $I_{S}$ =16A	-	1	1.4	V
Reverse recovery time	t <sub>rr</sub>	I <sub>S</sub> =16A, V <sub>GS</sub> =0V dI <sub>F</sub> /dt=100A/us	-	208	-	ns
Reverse recovery charge	Q <sub>rr</sub>		-	1.63	-	uC

#### Note;

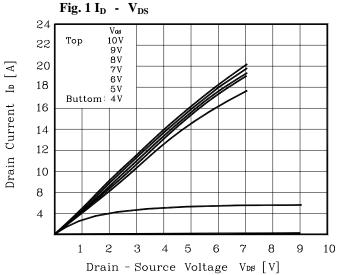
① Repetitive rating: Pulse width limited by maximum junction temperature

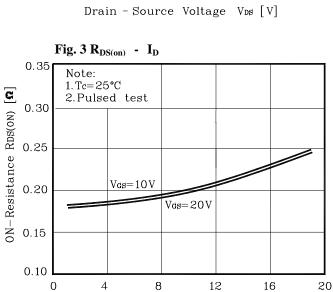
② L=3.0mH,  $I_{AS}$ =16A,  $V_{DD}$ =50V,  $R_{G}$ =25 $\Omega$ , Starting  $T_{J}$ =25 $^{\circ}$ C

③ Pulse Test : Pulse width≤300us, Duty cycle≤2%

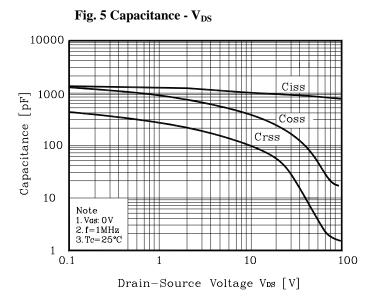
4 Essentially independent of operating temperature

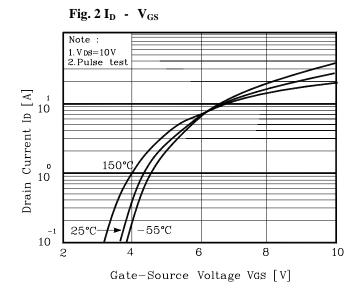
### **Electrical Characteristic Curves**

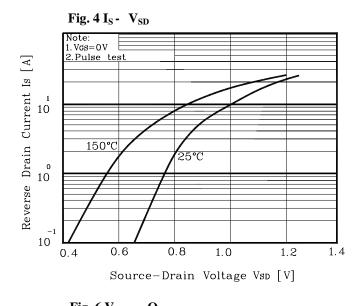


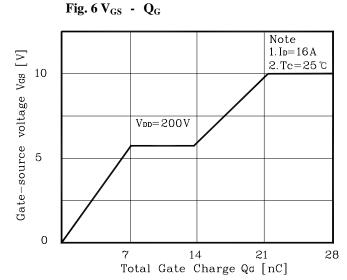


Drain Current ID [A]









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Fig. 7  $V_{DSS}\,\,$  -  $\,\,T_{J}$ 

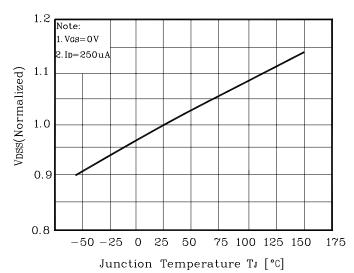


Fig. 9  $I_D - T_C$ 

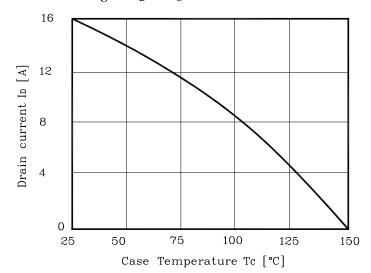


Fig. 8  $R_{DS(on)}\,\,$  -  $\,\,T_{J}$ 

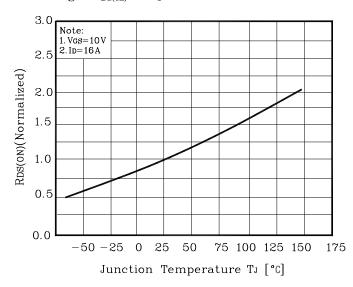


Fig. 10 Safe Operating Area

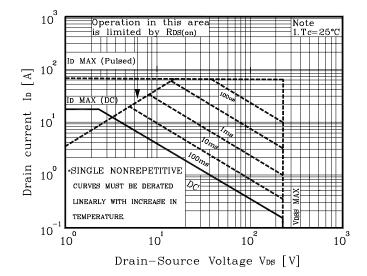


Fig. 11 Gate Charge Test Circuit & Waveform

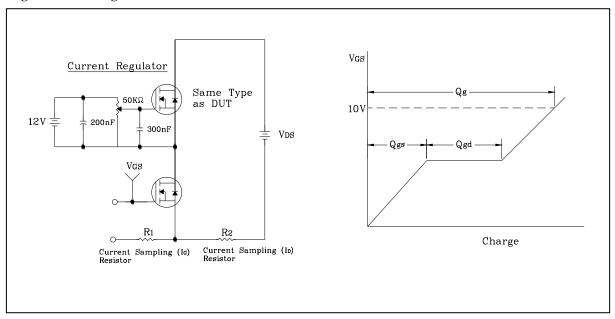


Fig. 12 Resistive Switching Test Circuit & Waveform

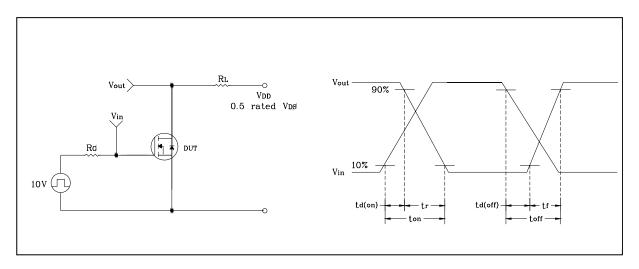
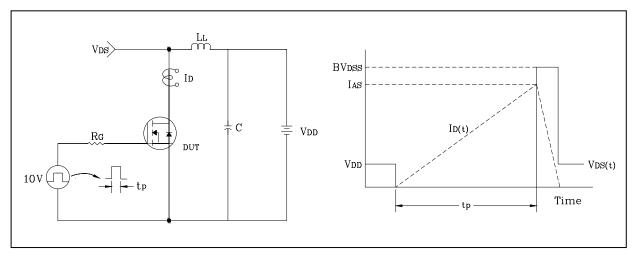
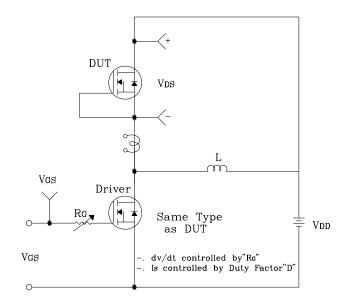


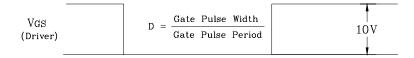
Fig. 13  $E_{AS}$  Test Circuit & Waveform

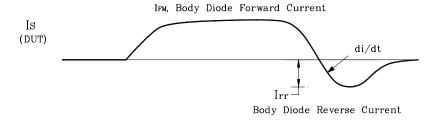


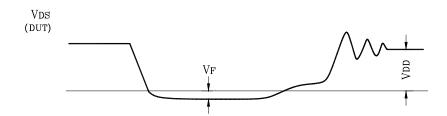
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Fig. 14 Diode Reverse Recovery Time Test Circuit & Waveform



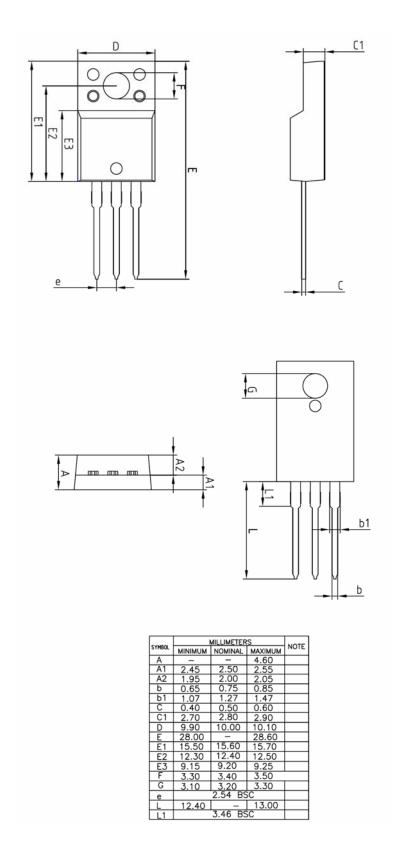






# **Outline Dimension**

unit: mm



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